Schottky barrier diode

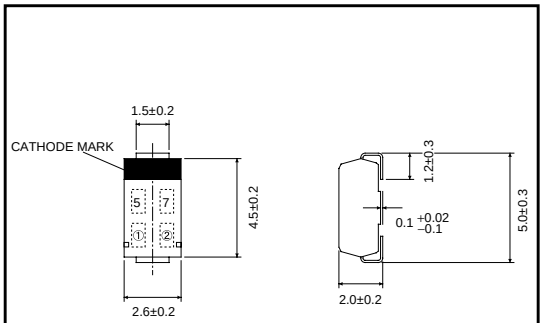
RB083L-20

●**Applications**
High frequency rectification
For switching power supply

●**Features**
1) Compact power mold type. (PMDS)
2) Ultra low V_F / Low I_R.
3) I_O=5A guaranteed despite the size.

●**Construction**
Silicon epitaxial planar

●**External dimensions** (Units : mm)



ROHM : PMDS
EIAJ : –
JEDEC : SOD-106 ①, ② ····· Date of manufacture EX. 1999.12 → 9,C

●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
Mean rectifying current *	I_O	5	A
Peak forward surge current (60Hz 1 ⌒)	I_{FSM}	70	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–40~+125	°C

* When mounted on alumina PCBs (82×30×1.0mm), Tc Max.=90°C

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.39	V	I_F=3.0A
Reverse current	I_R	–	–	500	μA	V_R=20V

● **Electrical characteristic curves** (Ta=25°C)

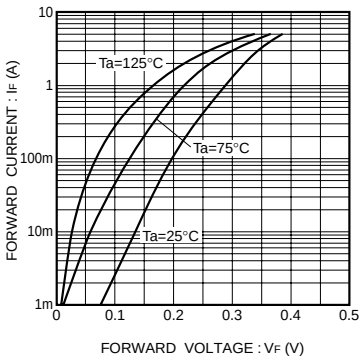


Fig.1 Forward characteristics

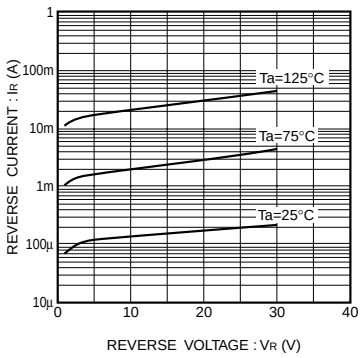


Fig.2 Reverse characteristics

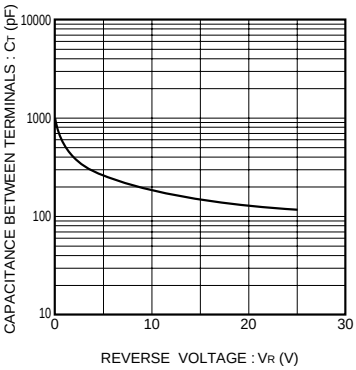


Fig.3 Cpacitance between terminals characteristics

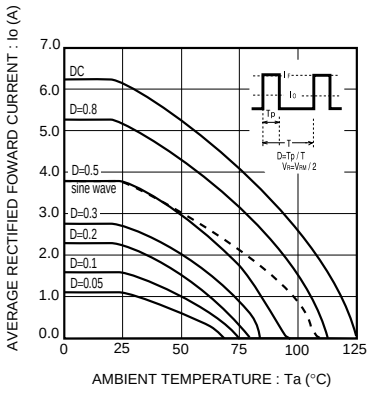


Fig.4 Derating curve (Io-Ta) (When mounted on alumina PCBs)

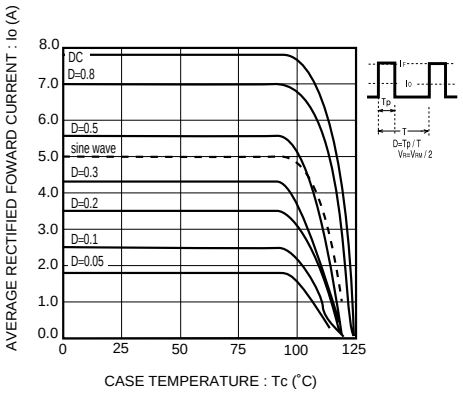


Fig.5 Derating curve (Io-Tc) (When mounted on alumina PCBs)